



安徽富信半导体科技有限公司

ANHUI FOSAN SEMICONDUCTOR TECHNOLOGY CO., LTD.

MUN2235

SOT-23 Digital Transistor 数字晶体管

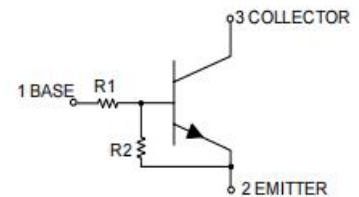
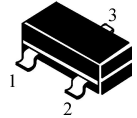
■ Features 特点

NPN With Bias Resistor Network
带偏置电阻

■ Absolute Maximum Ratings 最大额定值

SOT-23

- 1. BASE
- 2. EMITTER
- 3. COLLECTOR



Characteristic 特性参数	Symbol 符号	Rat 额定值	Unit 单位
Collector-Base Voltage 集电极基极电压	V_{CBO}	50	V
Collector-Emitter Voltage 集电极发射极电压	V_{CEO}	50	V
Collector Current 集电极电流	I_C	100	mA
Power dissipation 耗散功率	$P_C(T_a=25^\circ\text{C})$	246	mW
Thermal Resistance Junction-Ambient 热阻	$R_{\theta JA}$	508	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature 结温和储藏温度	T_J, T_{stg}	-55to+150 $^\circ\text{C}$	

■ Device Marking 产品打标

MUN2235=A8M

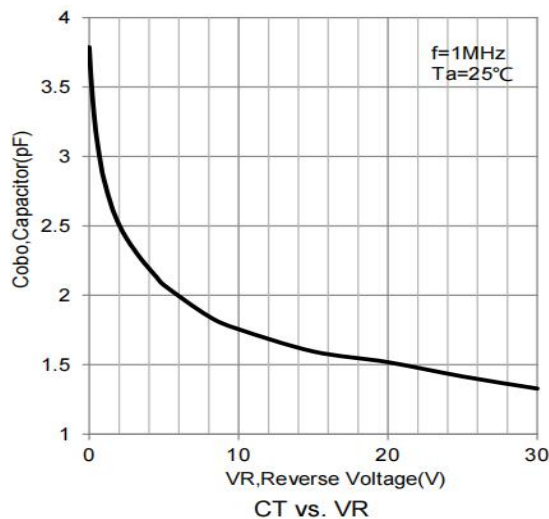
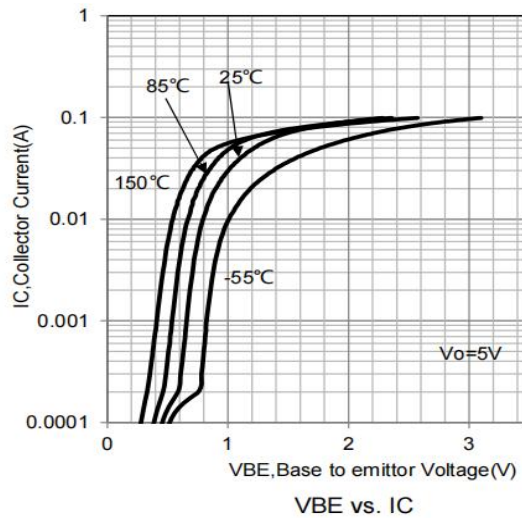
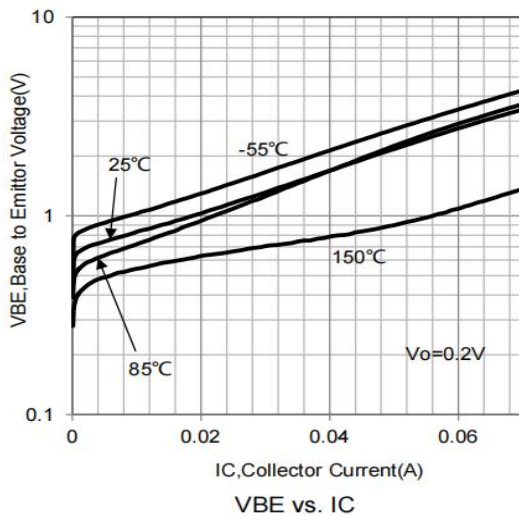
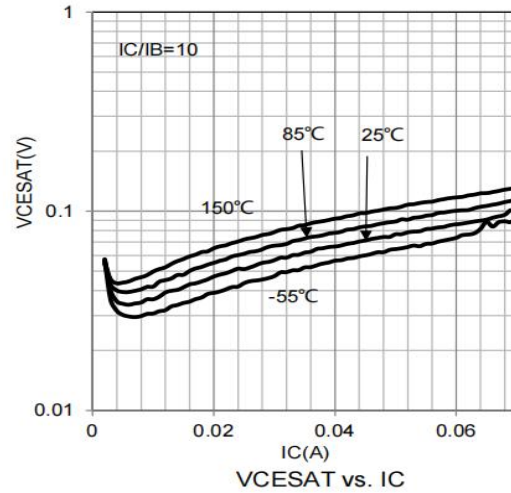
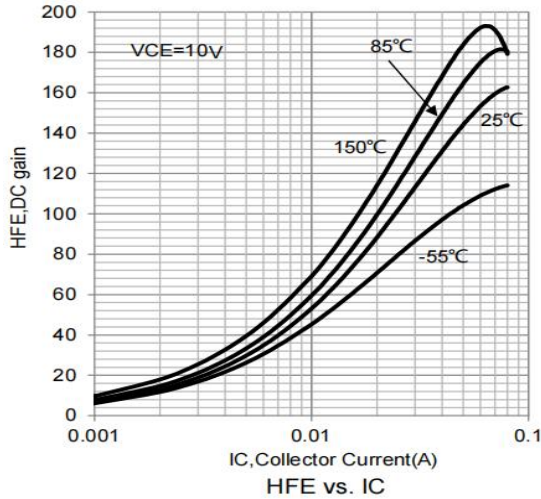


■ Electrical Characteristics 电特性

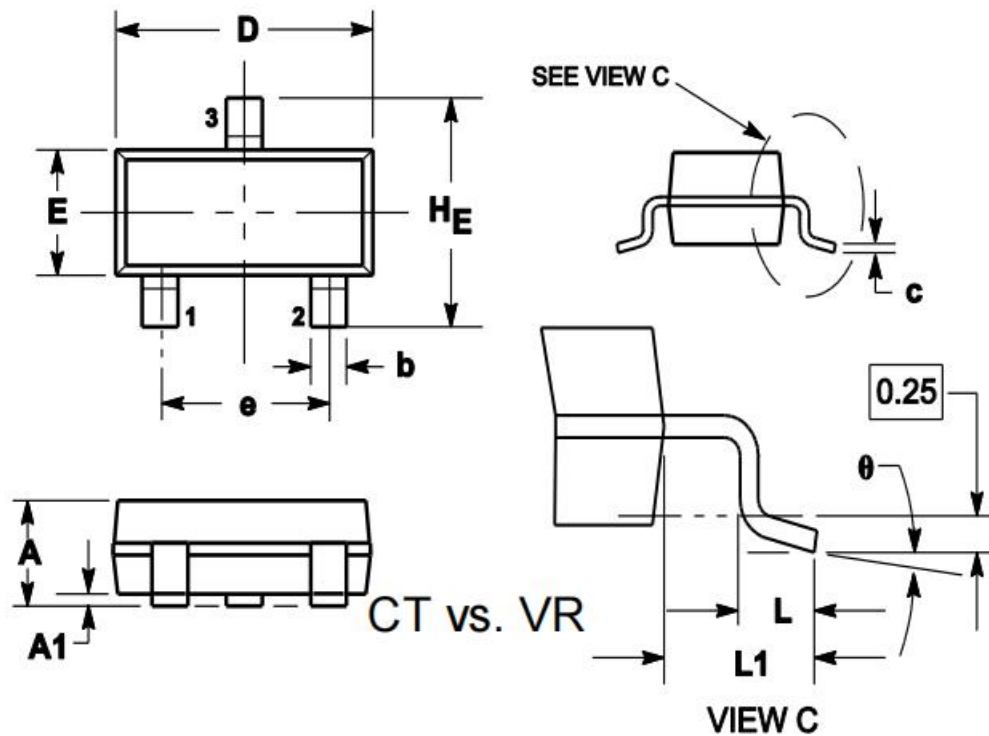
($T_A=25^{\circ}\text{C}$ unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	Min 最小值	Type 典型值	Max 最大值	Unit 单位
Collector-Base Breakdown Voltage 集电极基极击穿电压 ($I_C=10\mu\text{A}$, $I_E=0$)	BV_{CBO}	50	—	—	V
Collector-Emitter Breakdown Voltage 集电极发射极击穿电压 ($I_C=2\text{mA}$, $I_B=0$)	BV_{CEO}	50	—	—	V
Collector-Base Leakage Current 集电极基极漏电流 ($V_{CB}=50\text{V}$, $I_E=0$)	I_{CBO}	—	—	0.1	μA
Collector-Emitter Leakage Current 集电极发射极漏电流 ($V_{CE}=50\text{V}$, $I_E=0$)	I_{CEO}	—	—	0.5	μA
Emitter-Base Leakage Current 发射极基极漏电流 ($V_{EB}=6\text{V}$, $I_C=0$)	I_{EBO}	—	—	0.2	mA
DC Current Gain 直流电流增益 ($V_{CE}=10\text{V}$, $I_C=5\text{mA}$)	H_{FE}	80	—	—	
Collector-Emitter Saturation Voltage 集电极发射极饱和压降 ($I_C=10\text{mA}$, $I_B=1\text{mA}$)	$V_{CE(sat)}$	—	—	0.25	V
Output Voltage (on) 输出电压(导通) ($V_{CC} = 5.0\text{V}$, $V_B = 2.5\text{V}$, $R_L = 1.0\text{K}\Omega$)	V_{OL}	—	—	0.2	V
Output Voltage (on) 输出电压(导通) ($V_{CC} = 5.0\text{V}$, $V_B = 0.25\text{V}$, $R_L = 1.0\text{K}\Omega$)	V_{OH}	4.9	—	—	V
Input Resistor 输入电阻	R1	1.54	2.2	2.86	$\text{K}\Omega$
Resistor Ratio 电阻比率	R1/R2	0.038	—	0.056	

■ Typical Characteristic Curve 典型特性曲线



Dimension 外形封装尺寸



DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1	1.11	0.035	0.04	0.044
A1	0.01	0.06	0.1	0.001	0.002	0.004
b	0.37	0.44	0.5	0.015	0.018	0.02
c	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.9	3.04	0.11	0.114	0.12
E	1.20	1.3	1.4	0.047	0.051	0.055
e	1.78	1.9	2.04	0.07	0.075	0.081
L	0.10	0.2	0.3	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
HE	2.10	2.4	2.64	0.083	0.094	0.104
θ	0°	---	10°	0°	---	10°